

Application Serial No. 10/615,899
Reply to office action of September 22, 2006

PATENT
Docket: CU-3282

Amendments to the Claims

The listing of claims presented below will replace all prior versions, and listings, of claims in the application.

Listing of claims:

What is claimed is:

1. (Currently amended) A method for improving reliability of an etching apparatus and a deposition apparatus, which etching and deposition apparatus' use chlorine-containing etching and deposition gases respectively, the method comprising the steps of:

generating a plasma in the apparatus that ~~includes~~ consists essentially of hydrogen and nitrogen and 5% to 90% argon in the reaction unit to remove a chlorine-containing residual gas remaining in a reaction tube of the reaction unit.

2. (Cancelled)
3. (Cancelled)
4. (Cancelled)
5. (Cancelled)
6. (Cancelled)
7. (Cancelled)
8. (Cancelled)
9. (Cancelled)
10. (Cancelled)

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11. (Currently amended) A method for improving reliability of an etching apparatus and a deposition apparatus, which etching and deposition apparatus' use chlorine-containing etching and deposition gases respectively, the method comprising the steps of:

generating a plasma in the apparatus that ~~includes~~ consists essentially of nitrogen and 5% to 90% hydrogen in the reaction unit to remove a chlorine-containing residual gas that remains ~~remaining~~ in a reaction tube of the reaction unit.

12. (Currently amended) A method for improving reliability of an etching apparatus and a deposition apparatus, which etching and deposition apparatus' use chlorine-containing etching and deposition gases respectively, the method comprising the steps of:

generating a plasma in the apparatus that includes hydrogen and nitrogen in the reaction unit to remove a chlorine-containing residual gas remaining in a reaction tube of the reaction unit, wherein the plasma ~~including~~ consists essentially of nitrogen, ~~comprises~~ hydrogen of 5 to 50% and argon of 5 to 90%.